	V_{RSM}	100	V
Repetitive Peak Reverse Voltage	V_{RRM}	75	V
Repetitive Peak Forward Current	I _{FRM}	300	mA
Continuous Forward Current	Io	150	mA
Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 s Pulse Width = 1.0 μs	I _{FSM}	1.0 4.0	A
Operating Junction Temperature	TJ	+150	°C
Storage Temperature Range	T _{STG}	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS (Values are at $T_A = 25^{\circ}C$ unless otherwise noted.)

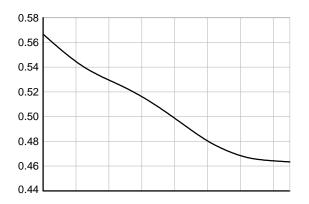
Symbol	Parameter	Value	Unit
P _D	Power Dissipation ($T_C = 25^{\circ}C$)	200	mW
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1)	500	°C/W

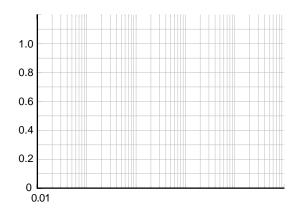
^{1.} Device mounted on FR-4 PCB minimum land pad.

ELECTRICAL CHARACTERISTICS (Values are at $T_{A} = 25^{\circ}$

1N4148WS, 1N4448WS, 1N914BWS

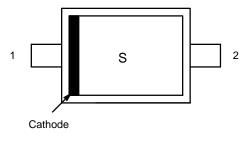
TYPICAL CHARACTERISTICS



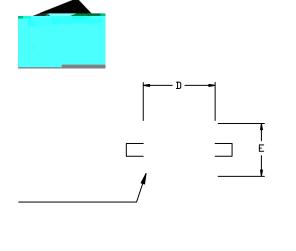


1N4148WS, 1N4448WS, 1N914BWS

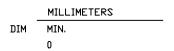
MARKING DIAGRAM











1. DIMENSIONING AND TOLERANCING PER ASME

4. DIMENSIONS D AND E DO NOT INCLUDE MONSONI

2. CONTROLLING DIMENSION: MILLIMETERS

3. LEAD THICK E MARK

